

# InGaAs Larger Area PIN Photodiode

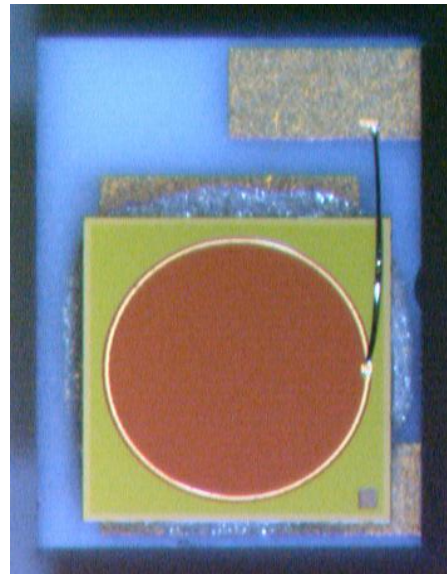
PDPF1000CC

## Applications

Optical Power Meter  
Infrared Rangefinder  
Spectroscopy

## Features

950 to 1625nm Spectral Response  
Planer Structure for High Reliability  
Low Dark Current  
High Sensitivity  
High Shunt Resistance  
Low Capacitance  
Chip-on-Carrier



## Description

Go!Foton large area Indium Gallium Arsenide (InGaAs) Photodiode consists of pin structure and photo sensitive area of 1 mm diameter with planer structure for high reliability. This PD has photo response in the near infrared spectrum range, between 950 and 1650 nm. This device has very high sensitivity and low noise, making it suitable for industrial application. The photodiode is mounted on ceramic subcarrier. PD chip is fabricated at Go!Foton proprietary wafer fab.

## Specifications

### Electro-Optical Characteristics

Parameter	Min	Typ	Max	Conditions
Active Area Diameter ( $\mu\text{m}$ )		1000		
Responsivity (A/W)	0.95			1.31 $\mu\text{m}$
	1.10			1.55 $\mu\text{m}$
Dark Current (nA)			50	$V_r = 2 \text{ V}$
Shunt Resistance ( $\text{M}\Omega$ )	50			$\pm 10 \text{ mV}$
Capacitance (pF)		100	150	$V_r = 0 \text{ V}$

Condition unless otherwise noted: 25°C



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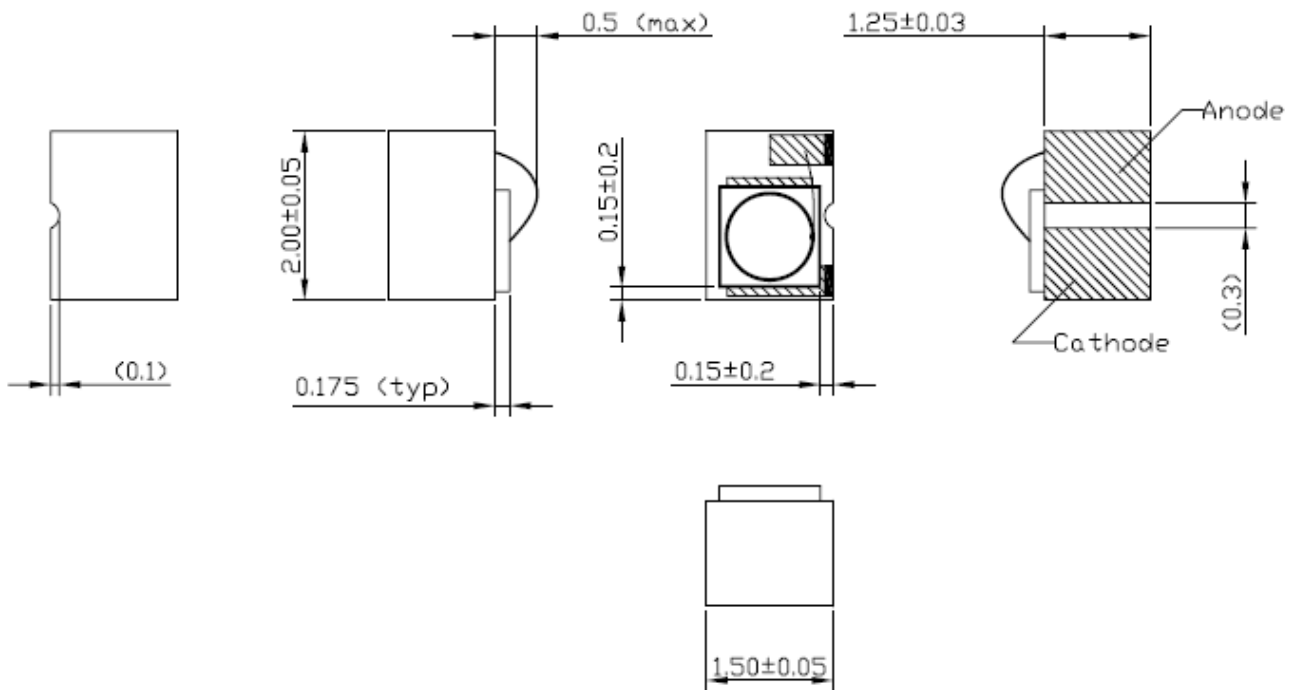
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## Absolute Maximum Rating

Parameter	Min	Typ	Max	Conditions
Reverse Voltage (V)			20	
Reverse Current (mA)			10	
Forward Current (mA)			10	
Maximum Input Power (mW)			10	
Operating Temperature (°C)	-40		85	
Storage Temperature (°C)	-40		85	
Electrostatic Discharge (V)			500	HBM

## Drawing



(mm)